
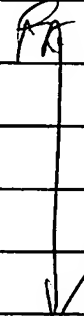


U.S. Patent Documents								
*Examiner Initials		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate	
	1.	5,168,331	12/01/92	Yilmaz	257	331		
	2.	5,216,275	06/01/93	Chen	257	493		
Foreign Patent Documents								
							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
Other Art (Including Author, Title, Date, Pertinent Pages, Etc.)								
	3.	Jongdae Kim et al., "High-Density Trench DMOSFETs Employing Two Step Trench Technique and Trench Contact Structure", ISPSD-2003 Proceedings, pp. 1-4						
	4.	Il-Yong Park et al., "Novel Process Techniques for Fabricating High Density Trench MOSFETs with Self-Aligned N ⁺ /P ⁺ Source Formed on the Trench Side Wall", ISPSD-2003 Proceedings, pp. 1-4.						
	5.	M.A.A. In 'tZandt, et al., "Record-low 4mΩ mm ² specific on-resistance for 20V Trench MOSFETs", ISPSD-2003 Proceedings, pp. 1-4.						
	6.	Mohamed Darwish et al., "A New Power W-Gated Trench MOSFET (WMOSFET) with High Switching Performance", ISPSD-2003 Proceedings, pp 1-4.						
	7.	Syotaro Ono et al., "30V New Fine Trench MOSFET with Ultra Low On-Resistance", ISPSD-2003 Proceedings, pp. 1-4.						

Examiner: <u>John Bal</u>	Date Considered: <u>1/13/05</u>
<p>* Examiner: Initial if reference is considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication with applicant.</p>	